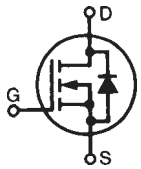
IXYS

TrenchT2™ Power MOSFET

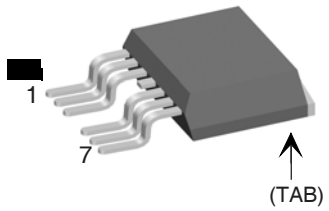
IXTA220N04T2-7

V_{DSS} = 40V
I_{D25} = 220A
$R_{DS(on)}$ ≤ 3.5mΩ

N-Channel Enhancement Mode
Avalanche Rated



TO-263 (7-lead)



Pins: 1 - Gate
2, 3 - Source
5,6,7 - Source
TAB (8) - Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	40	V
V_{DGR}	T_J = 25°C to 175°C, R_{GS} = 1MΩ	40	V
V_{GSM}	Transient	± 20	V
I_{D25}	T_C = 25°C	220	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	660	A
I_{AR}	T_C = 25°C	110	A
E_{AS}	T_C = 25°C	600	mJ
P_D	T_C = 25°C	360	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	1.6mm (0.062in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10 seconds	260	°C
Weight		3	g

Symbol	Test Conditions (T_J = 25°C unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	40			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	2.0		4.0	V
I_{GSS}	V_{GS} = ± 20V, V_{DS} = 0V			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$			5	μA
	V_{GS} = 0V T_J = 150°C			50	μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 50A, Notes 1, 2		2.8	3.5	mΩ

Features

- International standard package
- 175°C Operating Temperature
- High current handling capability
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-mode power supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

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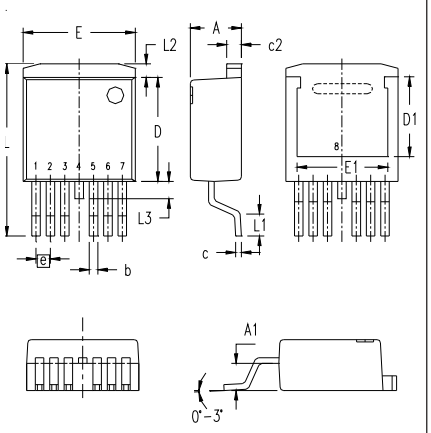
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	40	66		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		6820		pF
C_{oss}			1185		pF
C_{rss}			250		pF
$t_{d(on)}$	**Resistive Switching Times**		15		ns
t_r	V_{GS} = 10V, V_{DS} = 20V, I_D = 50A		21		ns
$t_{d(off)}$	R_G = 3.3Ω (External)		31		ns
t_f			21		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		112		nC
Q_{gs}			33		nC
Q_{gd}			30		nC
R_{thJC}				0.42	°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			220	A
I_{SM}	Repetitive, Pulse width limited by T_{JM}			660	A
V_{SD}	I_F = 50A, V_{GS} = 0V, Note 1			1.0	V
t_{rr}	I_F = 110A, V_{GS} = 0V		45		ns
I_{RM}	-di/dt = 100A/μs		1.4		A
Q_{RM}	V_R = 20V		32		nC

TO-263 (7-lead) (IXTA..7) Outline



Pins: 1 - Gate
2, 3 - Source
4 - Drain
5,6,7 - Source
Tab (8) - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETER MIN	MILLIMETER MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

Notes: 1. Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ 25ºC

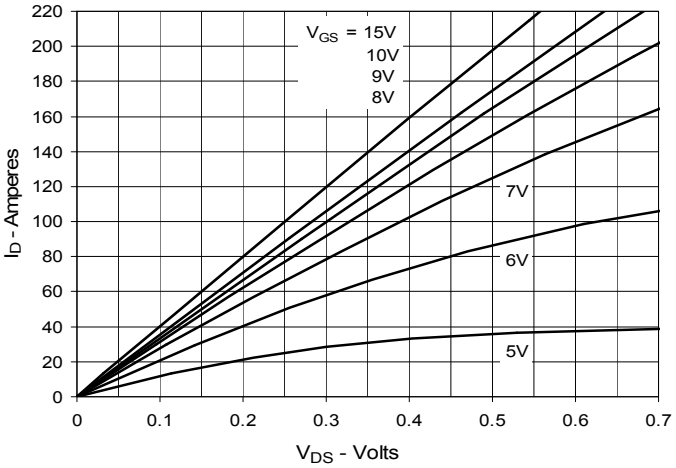


Fig. 2. Extended Output Characteristics @ 25ºC

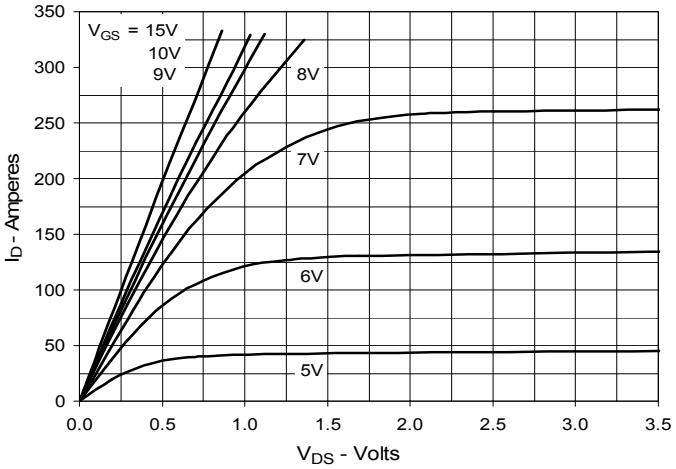


Fig. 3. Output Characteristics @ 150ºC

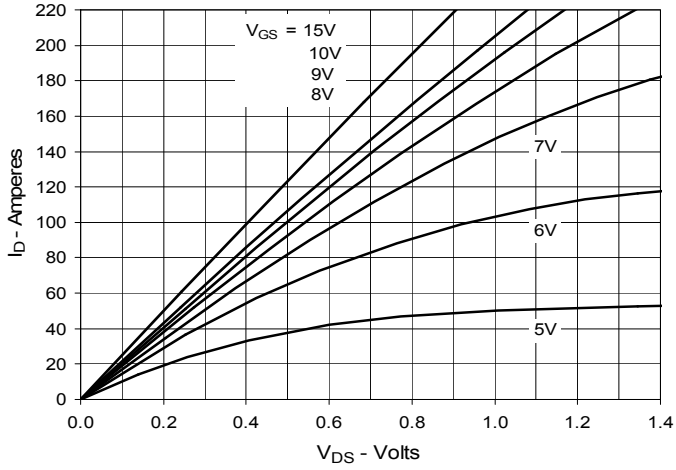


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 110A Value vs. Junction Temperature

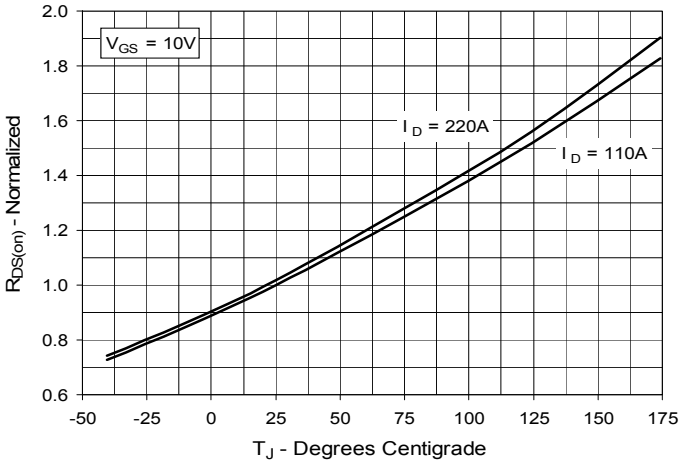


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 110A Value vs. Drain Current

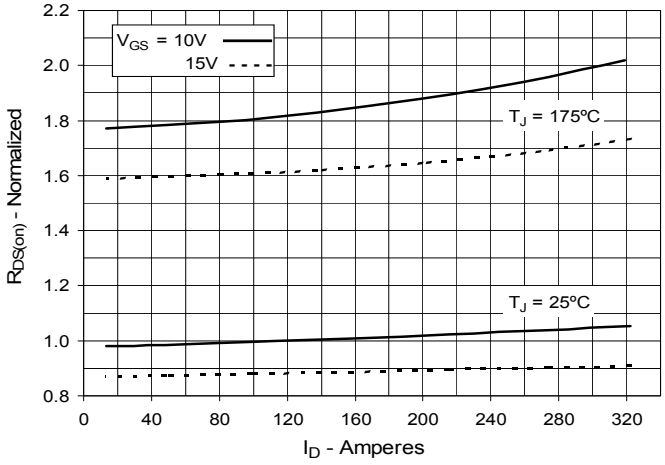


Fig. 6. Drain Current vs. Case Temperature

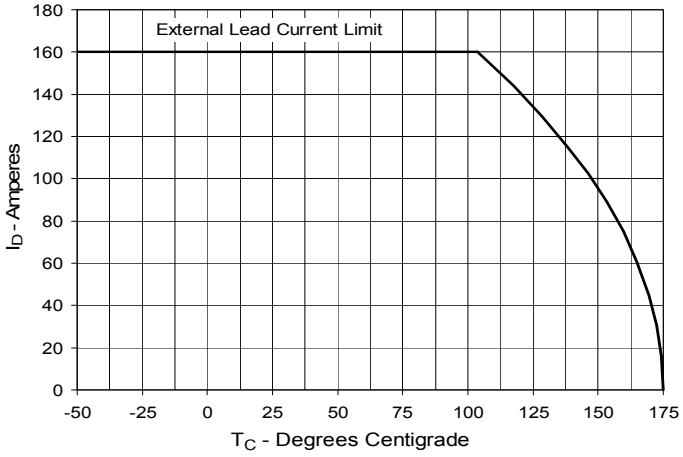


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Fig. 7. Input Admittance

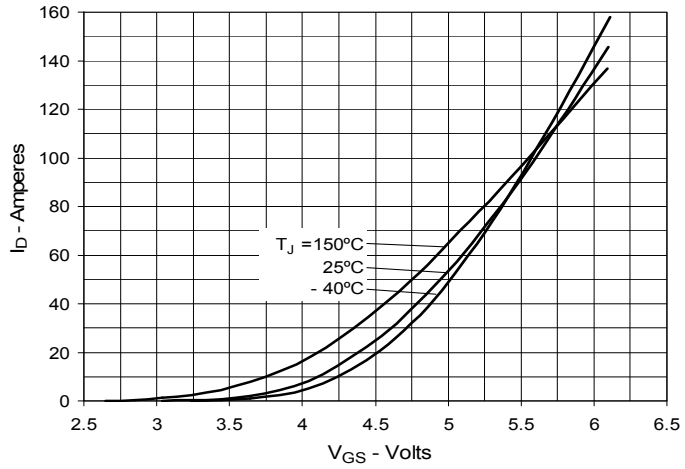

Fig. 8. Transconductance

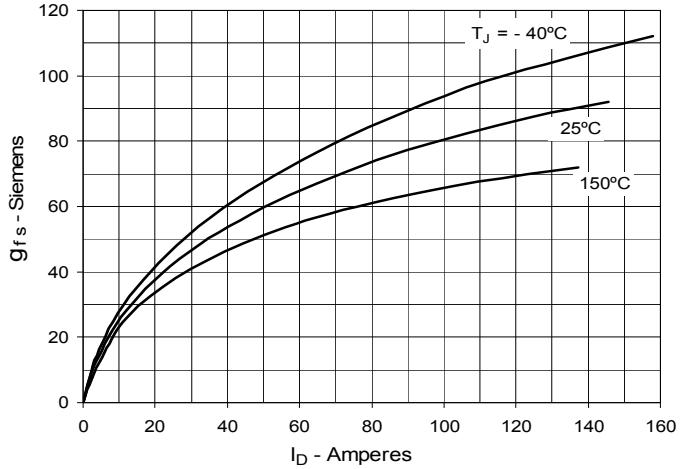

Fig. 9. Forward Voltage Drop of Intrinsic Diode

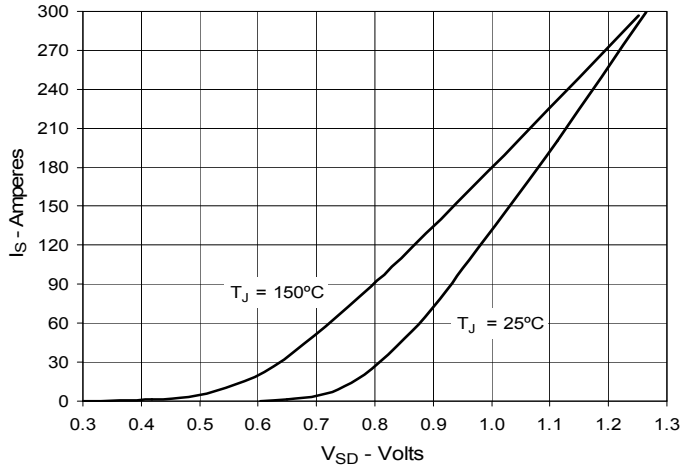

Fig. 10. Gate Charge

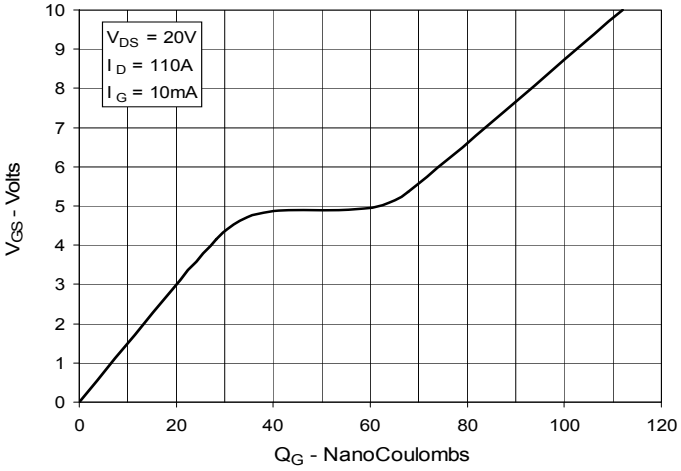

Fig. 11. Capacitance

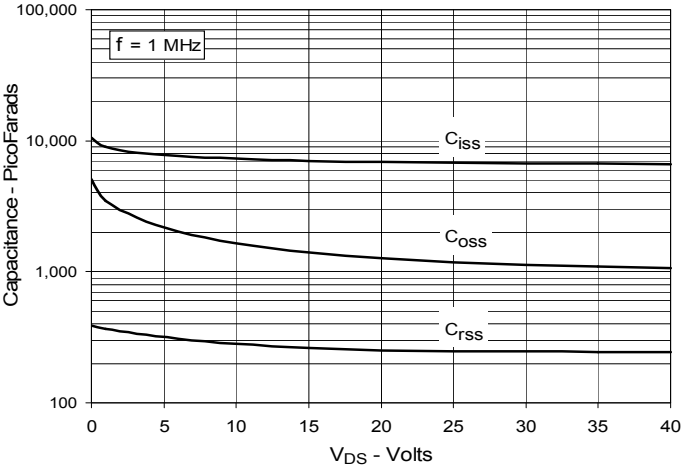

Fig. 12. Forward-Bias Safe Operating Area

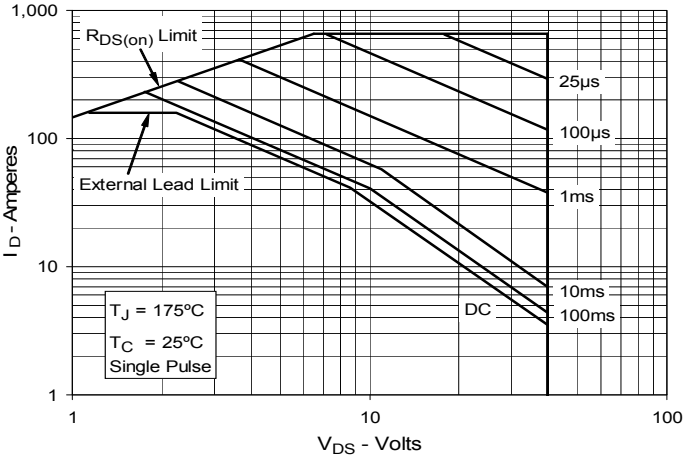

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Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

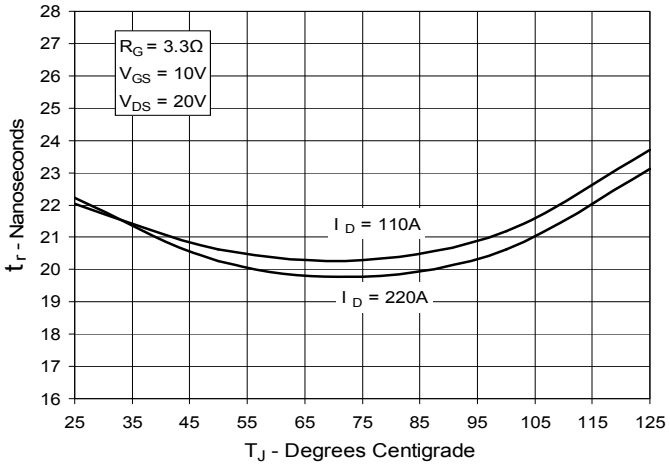

Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

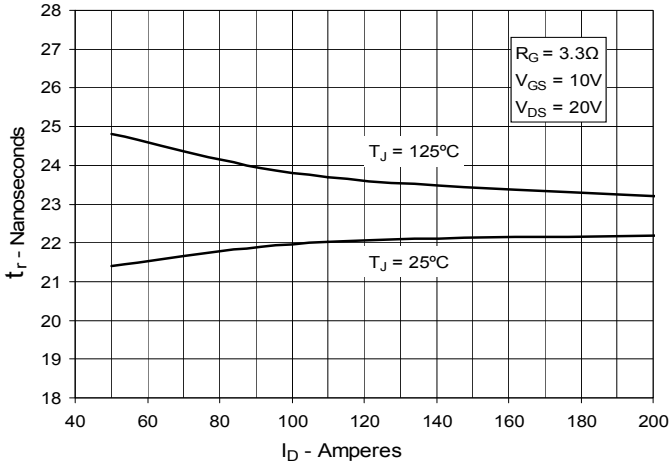

Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

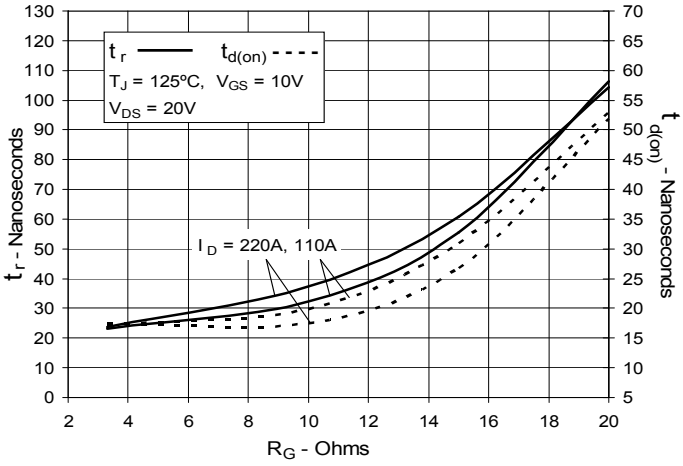

Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

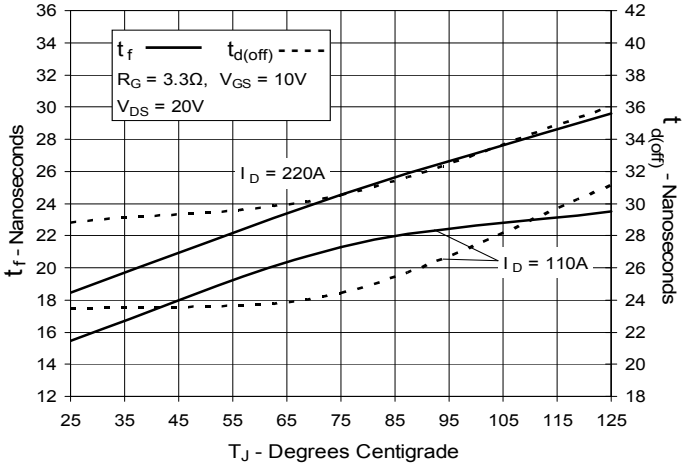

Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

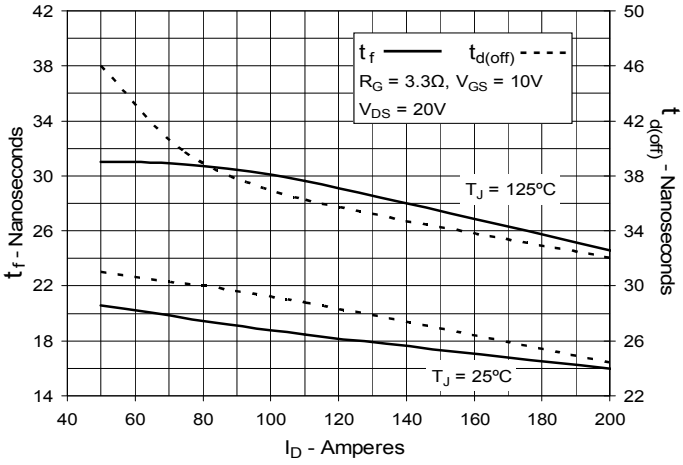

Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

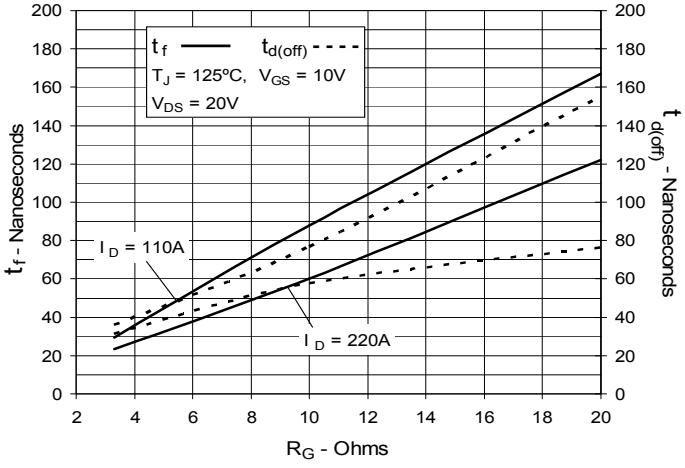

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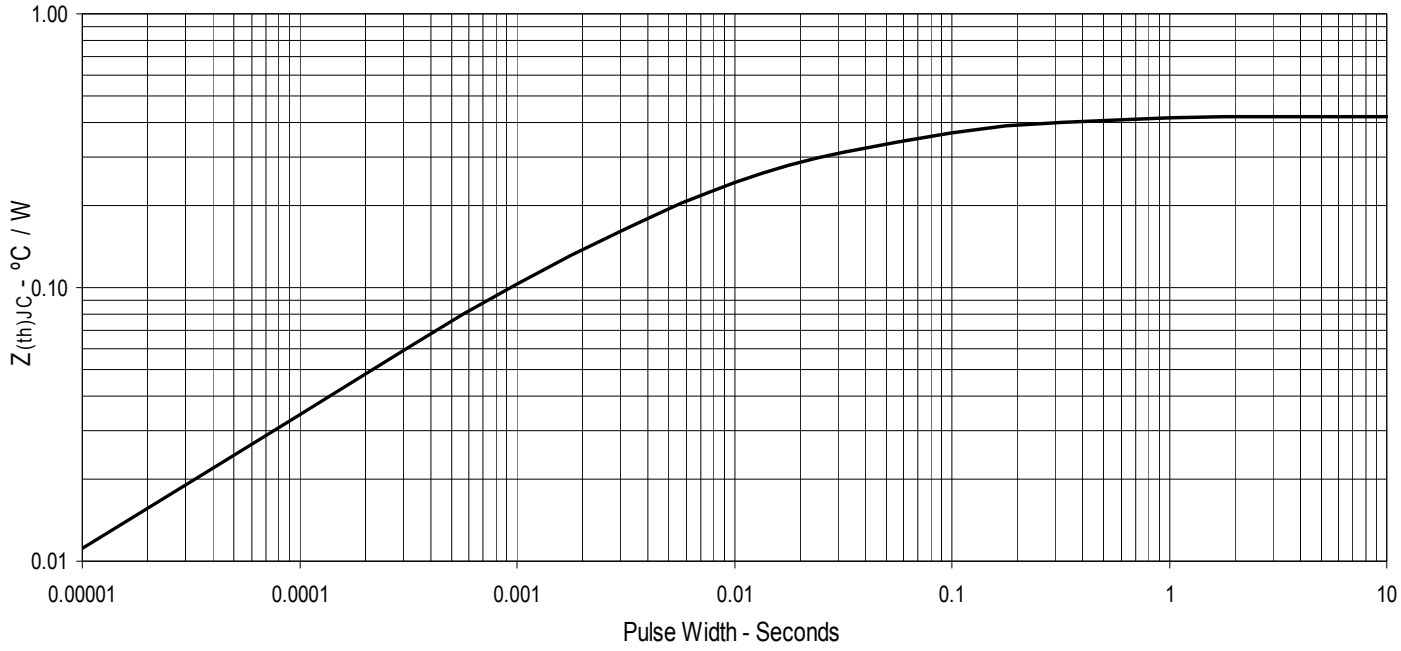
Fig. 19. Maximum Transient Thermal Impedance



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